MMG150S120UZ6TN

1200V 150A IGBT Module

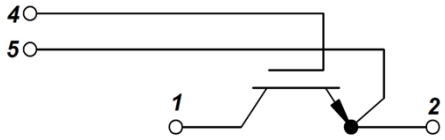
April 2015 **Version 01** **RoHS Compliant**

PRODUCT FEATURES

- ☐ IGBT^3 Chip(Trench+Field Stop technology)
- ☐ Low switching losses
- ☐ Low saturation voltage and positive temperature coefficient
- ☐ Fast switching and short tail current

APPLICATIONS

- ☐ AC motor control
- ☐ Motion/servo control
- ☐ Inverter and power supplies



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ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃	1200	V
V_{GES}	Gate Emitter Voltage		±20	
I_C	DC Collector Current	T_C=25℃	200	A
		T_C=80℃	150	
I_{CM}	Repetitive Peak Collector Current	tp=1ms	300	
P_{tot}	Power Dissipation Per IGBT		650	W

MODULE CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		150	℃
T_{Jop}	Operating Temperature		-40~125	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
Torque	to heatsink	Recommended（M6）	3~5	Nm
	to terminal	Recommended（M5）	2.5~5	Nm
Weight			160	g

MacMic Science & Technology Co., Ltd.

Add：#18, Hua Shan Zhong Lu, New District, Changzhou City, Jiangsu Province, P. R .of China

Tel.：+86-519-85163708 Fax：+86-519-85162291 Post Code：213022 Website：www.macmicst.com

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=6mA		5	5.8	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=150A, V_{GE}=15V, T_J=25℃			1.7	2.15	
		I_C=150A, V_{GE}=15V, T_J=125℃			1.9		
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25℃				100	μA
		V_{CE}=1200V, V_{GE}=0V, T_J=125℃				1	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±15V, T_J=125℃		-400		400	nA
R_{gint}	Integrated Gate Resistor				5		Ω
Q_g	Gate Charge	V_{CE}=600V, I_C=150A , V_{GE}=15V			1.4		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			10.5		nF
C_{res}	Reverse Transfer Capacitance				0.4		nF
$t_{d(on)}$	Turn on Delay Time	V_{CC}=600V,I_C=150A R_G =2.4Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		260		ns
			T_J=125℃		290		ns
t_r	Rise Time		T_J=25℃		30		ns
			T_J=125℃		50		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=600V,I_C=150A R_G =2.4Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		420		ns
			T_J=125℃		520		ns
t_f	Fall Time		T_J=25℃		70		ns
			T_J=125℃		90		ns
E_{on}	Turn on Energy	V_{CC}=600V,I_C=150A R_G =2.4Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		12		mJ
			T_J=125℃		16		mJ
E_{off}	Turn off Energy		T_J=25℃		11		mJ
			T_J=125℃		14.5		mJ
I_{SC}	Short Circuit Current	tpsc≤10μS , V_{GE}=15V T_J=125℃,V_{CC}=600V			600		A
R_{thJC}	Junction to Case Thermal Resistance （Per IGBT）					0.19	K /W

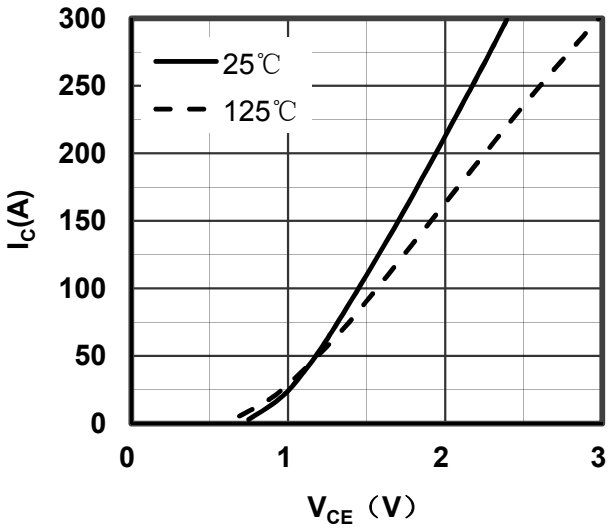


Figure 1. Typical Output Characteristics IGBT

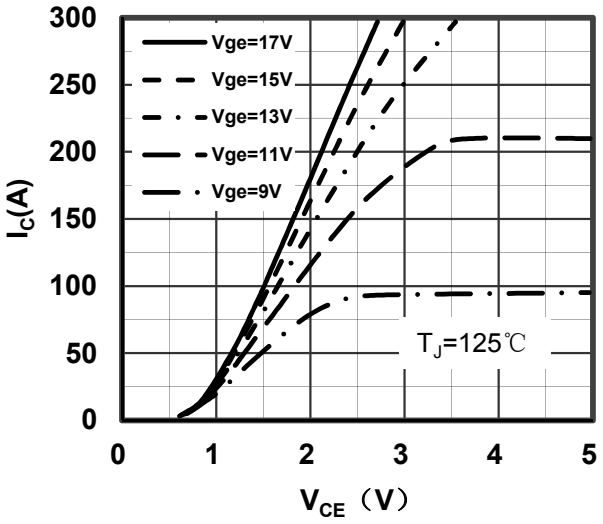


Figure 2. Typical Output Characteristics IGBT

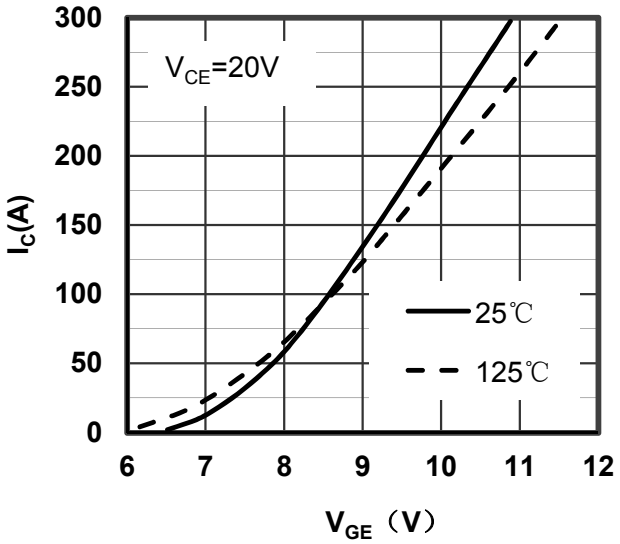


Figure 3. Typical Transfer characteristics IGBT

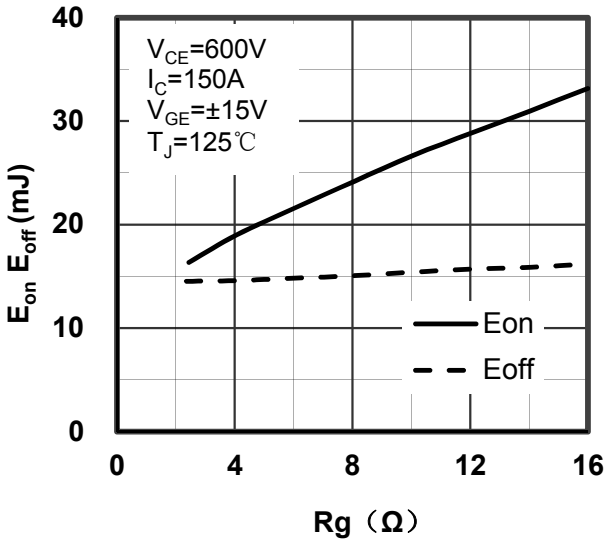


Figure 4. Switching Energy vs Gate Resistor IGBT

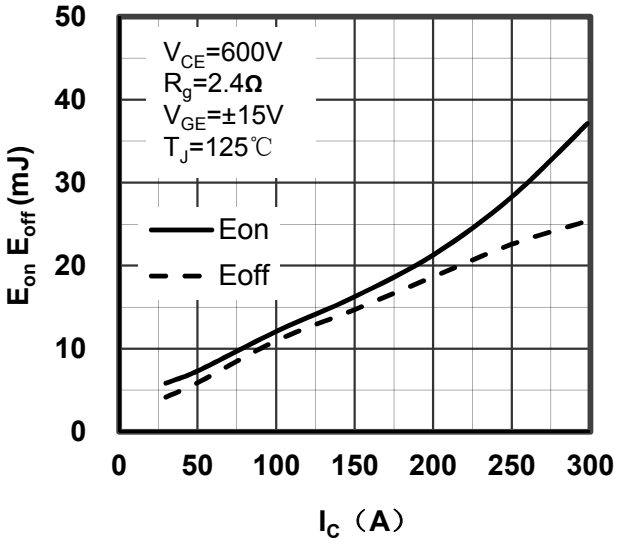


Figure 5. Switching Energy vs Collector Current IGBT

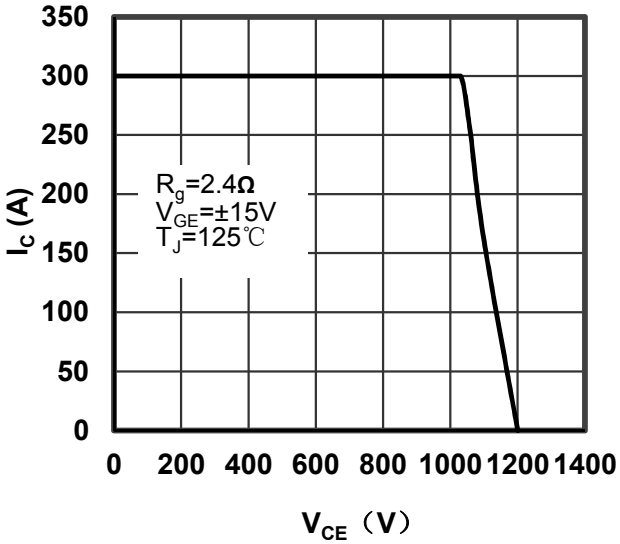


Figure 6. Reverse Biased Safe Operating Area IGBT

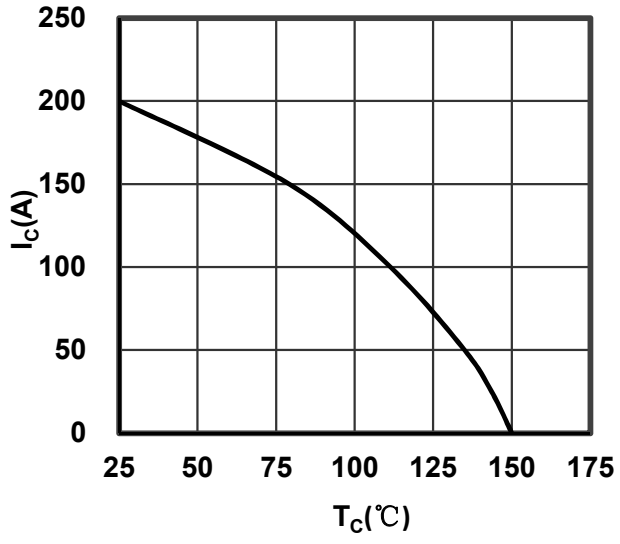


Figure 7. Collector Current vs Case temperature

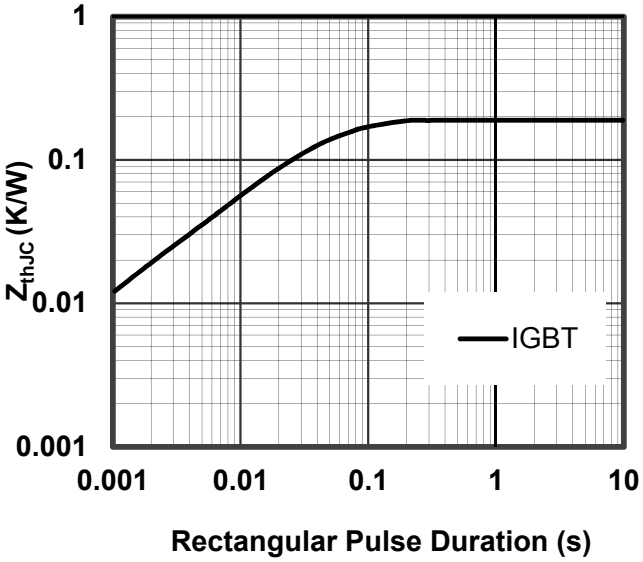
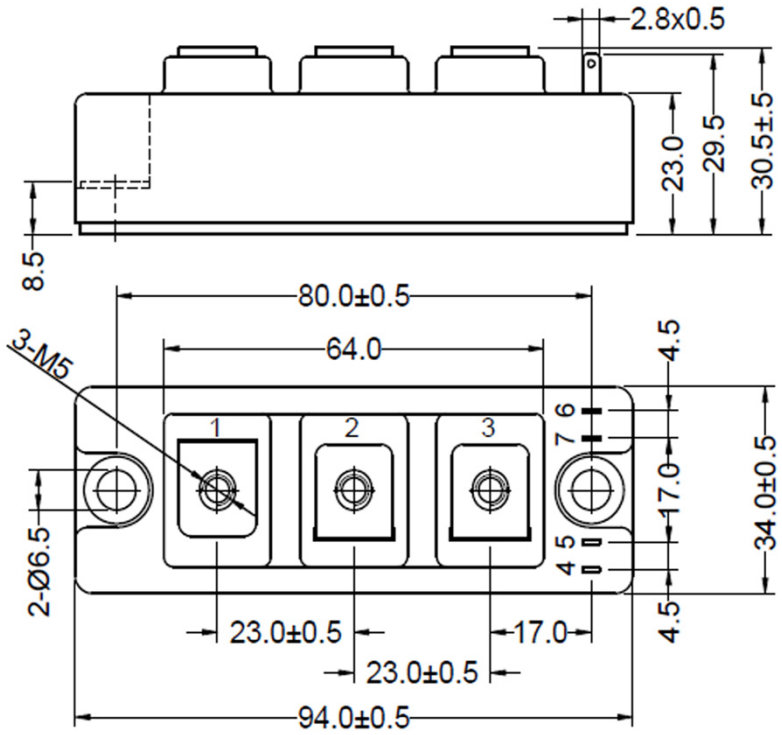


Figure 8. Transient Thermal Impedance of IGBT



Dimensions in (mm)

Figure 9. Package Outline